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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	48
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	12K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 12x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LFQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f101lgafb-v0

O ROM, RAM capacities

Flash ROM	Data flash	RAM	RL78/G13					
			20 pins	24 pins	25 pins	30 pins	32 pins	36 pins
128 KB	8 KB	12 KB	—	—	—	R5F100AG	R5F100BG	R5F100CG
	—		—	—	—	R5F101AG	R5F101BG	R5F101CG
96 KB	8 KB	8 KB	—	—	—	R5F100AF	R5F100BF	R5F100CF
	—		—	—	—	R5F101AF	R5F101BF	R5F101CF
64 KB	4 KB	4 KB Note	R5F1006E	R5F1007E	R5F1008E	R5F100AE	R5F100BE	R5F100CE
	—		R5F1016E	R5F1017E	R5F1018E	R5F101AE	R5F101BE	R5F101CE
48 KB	4 KB	3 KB Note	R5F1006D	R5F1007D	R5F1008D	R5F100AD	R5F100BD	R5F100CD
	—		R5F1016D	R5F1017D	R5F1018D	R5F101AD	R5F101BD	R5F101CD
32 KB	4 KB	2 KB	R5F1006C	R5F1007C	R5F1008C	R5F100AC	R5F100BC	R5F100CC
	—		R5F1016C	R5F1017C	R5F1018C	R5F101AC	R5F101BC	R5F101CC
16 KB	4 KB	2 KB	R5F1006A	R5F1007A	R5F1008A	R5F100AA	R5F100BA	R5F100CA
	—		R5F1016A	R5F1017A	R5F1018A	R5F101AA	R5F101BA	R5F101CA

Flash ROM	Data flash	RAM	RL78/G13							
			40 pins	44 pins	48 pins	52 pins	64 pins	80 pins	100 pins	128 pins
512 KB	8 KB	32 KB Note	—	R5F100FL	R5F100GL	R5F100JL	R5F100LL	R5F100ML	R5F100PL	R5F100SL
	—		—	R5F101FL	R5F101GL	R5F101JL	R5F101LL	R5F101ML	R5F101PL	R5F101SL
384 KB	8 KB	24 KB	—	R5F100FK	R5F100GK	R5F100JK	R5F100LK	R5F100MK	R5F100PK	R5F100SK
	—		—	R5F101FK	R5F101GK	R5F101JK	R5F101LK	R5F101MK	R5F101PK	R5F101SK
256 KB	8 KB	20 KB Note	—	R5F100FJ	R5F100GJ	R5F100JJ	R5F100LJ	R5F100MJ	R5F100PJ	R5F100SJ
	—		—	R5F101FJ	R5F101GJ	R5F101JJ	R5F101LJ	R5F101MJ	R5F101PJ	R5F101SJ
192 KB	8 KB	16 KB	R5F100EH	R5F100FH	R5F100GH	R5F100JH	R5F100LH	R5F100MH	R5F100PH	R5F100SH
	—		R5F101EH	R5F101FH	R5F101GH	R5F101JH	R5F101LH	R5F101MH	R5F101PH	R5F101SH
128 KB	8 KB	12 KB	R5F100EG	R5F100FG	R5F100GG	R5F100JG	R5F100LG	R5F100MG	R5F100PG	—
	—		R5F101EG	R5F101FG	R5F101GG	R5F101JG	R5F101LG	R5F101MG	R5F101PG	—
96 KB	8 KB	8 KB	R5F100EF	R5F100FF	R5F100GF	R5F100JF	R5F100LF	R5F100MF	R5F100PF	—
	—		R5F101EF	R5F101FF	R5F101GF	R5F101JF	R5F101LF	R5F101MF	R5F101PF	—
64 KB	4 KB	4 KB Note	R5F100EE	R5F100FE	R5F100GE	R5F100JE	R5F100LE	—	—	—
	—		R5F101EE	R5F101FE	R5F101GE	R5F101JE	R5F101LE	—	—	—
48 KB	4 KB	3 KB Note	R5F100ED	R5F100FD	R5F100GD	R5F100JD	R5F100LD	—	—	—
	—		R5F101ED	R5F101FD	R5F101GD	R5F101JD	R5F101LD	—	—	—
32 KB	4 KB	2 KB	R5F100EC	R5F100FC	R5F100GC	R5F100JC	R5F100LC	—	—	—
	—		R5F101EC	R5F101FC	R5F101GC	R5F101JC	R5F101LC	—	—	—
16 KB	4 KB	2 KB	R5F100EA	R5F100FA	R5F100GA	—	—	—	—	—
	—		R5F101EA	R5F101FA	R5F101GA	—	—	—	—	—

Note The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xD, R5F101xD (x = 6 to 8, A to C, E to G, J, L): Start address FF300H

R5F100xE, R5F101xE (x = 6 to 8, A to C, E to G, J, L): Start address FEF00H

R5F100xJ, R5F101xJ (x = F, G, J, L, M, P): Start address FAF00H

R5F100xL, R5F101xL (x = F, G, J, L, M, P, S): Start address F7F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

Table 1-1. List of Ordering Part Numbers

(1/12)

Pin count	Package	Data flash	Fields of Application ^{Note}	Ordering Part Number
20 pins	20-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)	Mounted	A	R5F1006AASP#V0, R5F1006CASP#V0, R5F1006DASP#V0, R5F1006EASP#V0 R5F1006AASP#X0, R5F1006CASP#X0, R5F1006DASP#X0, R5F1006EASP#X0 R5F1006ADSP#V0, R5F1006CDSP#V0, R5F1006DDSP#V0, R5F1006EDSP#V0 R5F1006ADSP#X0, R5F1006CDSP#X0, R5F1006DDSP#X0, R5F1006EDSP#X0 R5F1006AGSP#V0, R5F1006CGSP#V0, R5F1006DGSP#V0, R5F1006EGSP#V0 R5F1006AGSP#X0, R5F1006CGSP#X0, R5F1006DGSP#X0, R5F1006EGSP#X0
			D	R5F1006ADSP#V0, R5F1006CDSP#V0, R5F1006DDSP#V0, R5F1006EDSP#V0 R5F1006ADSP#X0, R5F1006CDSP#X0, R5F1006DDSP#X0, R5F1006EDSP#X0 R5F1006AGSP#V0, R5F1006CGSP#V0, R5F1006DGSP#V0, R5F1006EGSP#V0 R5F1006AGSP#X0, R5F1006CGSP#X0, R5F1006DGSP#X0, R5F1006EGSP#X0
			G	R5F1016AASP#V0, R5F1016CASP#V0, R5F1016DASP#V0, R5F1016EASP#V0 R5F1016AASP#X0, R5F1016CASP#X0, R5F1016DASP#X0, R5F1016EASP#X0 R5F1016ADSP#V0, R5F1016CDSP#V0, R5F1016DDSP#V0, R5F1016EDSP#V0 R5F1016ADSP#X0, R5F1016CDSP#X0, R5F1016DDSP#X0, R5F1016EDSP#X0
		Not mounted	A	R5F1016AASP#V0, R5F1016CASP#V0, R5F1016DASP#V0, R5F1016EASP#V0 R5F1016AASP#X0, R5F1016CASP#X0, R5F1016DASP#X0, R5F1016EASP#X0 R5F1016ADSP#V0, R5F1016CDSP#V0, R5F1016DDSP#V0, R5F1016EDSP#V0 R5F1016ADSP#X0, R5F1016CDSP#X0, R5F1016DDSP#X0, R5F1016EDSP#X0
			D	R5F1016ADSP#V0, R5F1016CDSP#V0, R5F1016DDSP#V0, R5F1016EDSP#V0 R5F1016ADSP#X0, R5F1016CDSP#X0, R5F1016DDSP#X0, R5F1016EDSP#X0
			G	R5F1007AANA#U0, R5F1007CANA#U0, R5F1007DANA#U0, R5F1007EANA#U0 R5F1007AANA#W0, R5F1007CANA#W0, R5F1007DANA#W0, R5F1007EANA#W0 R5F1007ADNA#U0, R5F1007CDNA#U0, R5F1007DDNA#U0, R5F1007EDNA#U0 R5F1007ADNA#W0, R5F1007CDNA#W0, R5F1007DDNA#W0, R5F1007EDNA#W0 R5F1007AGNA#U0, R5F1007CGNA#U0, R5F1007DGNA#U0, R5F1007EGNA#U0 R5F1007AGNA#W0, R5F1007CGNA#W0, R5F1007DGNA#W0, R5F1007EGNA#W0
		Not mounted	A	R5F1017AANA#U0, R5F1017CANA#U0, R5F1017DANA#U0, R5F1017EANA#U0 R5F1017AANA#W0, R5F1017CANA#W0, R5F1017DANA#W0, R5F1017EANA#W0 R5F1017ADNA#U0, R5F1017CDNA#U0, R5F1017DDNA#U0, R5F1017EDNA#U0 R5F1017ADNA#W0, R5F1017CDNA#W0, R5F1017DDNA#W0, R5F1017EDNA#W0
			D	R5F1017ADNA#U0, R5F1017CDNA#U0, R5F1017DDNA#U0, R5F1017EDNA#U0 R5F1017ADNA#W0, R5F1017CDNA#W0, R5F1017DDNA#W0, R5F1017EDNA#W0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

Table 1-1. List of Ordering Part Numbers

(4/12)

Pin count	Package	Data flash	Fields of Application <small>Note</small>	Ordering Part Number
44 pins	44-pin plastic LQFP (10 × 10 mm, 0.8 mm pitch)	Mounted	A D G	R5F100FAAFP#V0, R5F100FC AFP#V0, R5F100FDAFP#V0, R5F100FEA FP#V0, R5F100FFA FP#V0, R5F100FGA FP#V0, R5F100FH A FP#V0, R5F100FJA FP#V0, R5F100FKA FP#V0, R5F100FLA FP#V0 R5F100FAAFP#X0, R5F100FC AFP#X0, R5F100FDAFP#X0, R5F100FEA FP#X0, R5F100FFA FP#X0, R5F100FGA FP#X0, R5F100FH A FP#X0, R5F100FJA FP#X0, R5F100FKA FP#X0, R5F100FLA FP#X0 R5F100FADFP#V0, R5F100FCDFP#V0, R5F100FDDFP#V0, R5F100FEDFP#V0, R5F100FFDFP#V0, R5F100FGDFP#V0, R5F100FHDFP#V0, R5F100FJDFP#V0, R5F100FKDFP#V0, R5F100FLDFP#V0 R5F100FADFP#X0, R5F100FCDFP#X0, R5F100FDDFP#X0, R5F100FEDFP#X0, R5F100FFDFP#X0, R5F100FGDFP#X0, R5F100FHDFP#X0, R5F100FJDFP#X0, R5F100FKDFP#X0, R5F100FLDFP#X0 R5F100FAGFP#V0, R5F100FC GFP#V0, R5F100FD GFP#V0, R5F100FEGFP#V0, R5F100FF GFP#V0, R5F100FG GFP#V0, R5F100FH GFP#V0, R5F100FJ GFP#V0 R5F100FAGFP#X0, R5F100FC GFP#X0, R5F100FD GFP#X0, R5F100FEGFP#X0, R5F100FF GFP#X0, R5F100FG GFP#X0, R5F100FH GFP#X0, R5F100FJ GFP#X0 Not mounted
			A D	R5F101FAAFP#V0, R5F101FC AFP#V0, R5F101FDAFP#V0, R5F101FEA FP#V0, R5F101FFA FP#V0, R5F101FGA FP#V0, R5F101FH A FP#V0, R5F101FJA FP#V0, R5F101FKA FP#V0, R5F101FLA FP#V0 R5F101FAAFP#X0, R5F101FC AFP#X0, R5F101FDAFP#X0, R5F101FEA FP#X0, R5F101FFA FP#X0, R5F101FGA FP#X0, R5F101FH A FP#X0, R5F101FJA FP#X0, R5F101FKA FP#X0, R5F101FLA FP#X0 R5F101FADFP#V0, R5F101FCDFP#V0, R5F101FDDFP#V0, R5F101FEDFP#V0, R5F101FFDFP#V0, R5F101FGDFP#V0, R5F101FHDFP#V0, R5F101FJDFP#V0, R5F101FKDFP#V0, R5F101FLDFP#V0 R5F101FADFP#X0, R5F101FCDFP#X0, R5F101FDDFP#X0, R5F101FEDFP#X0, R5F101FFDFP#X0, R5F101FGDFP#X0, R5F101FHDFP#X0, R5F101FJDFP#X0, R5F101FKDFP#X0, R5F101FLDFP#X0

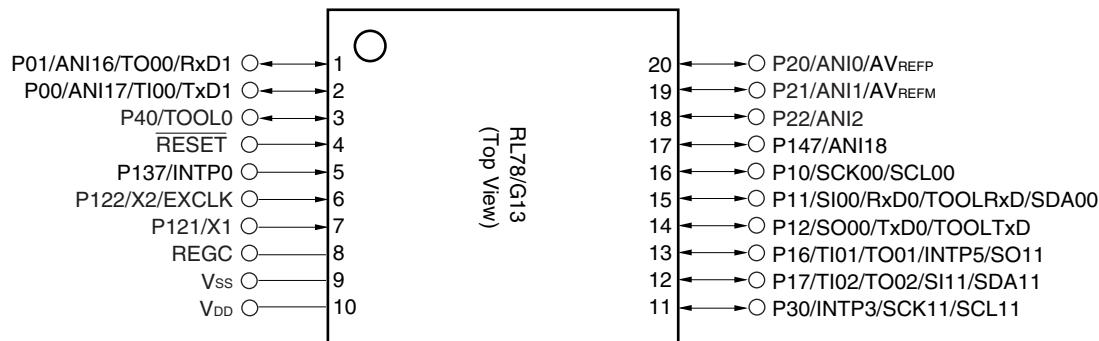
Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3 Pin Configuration (Top View)

1.3.1 20-pin products

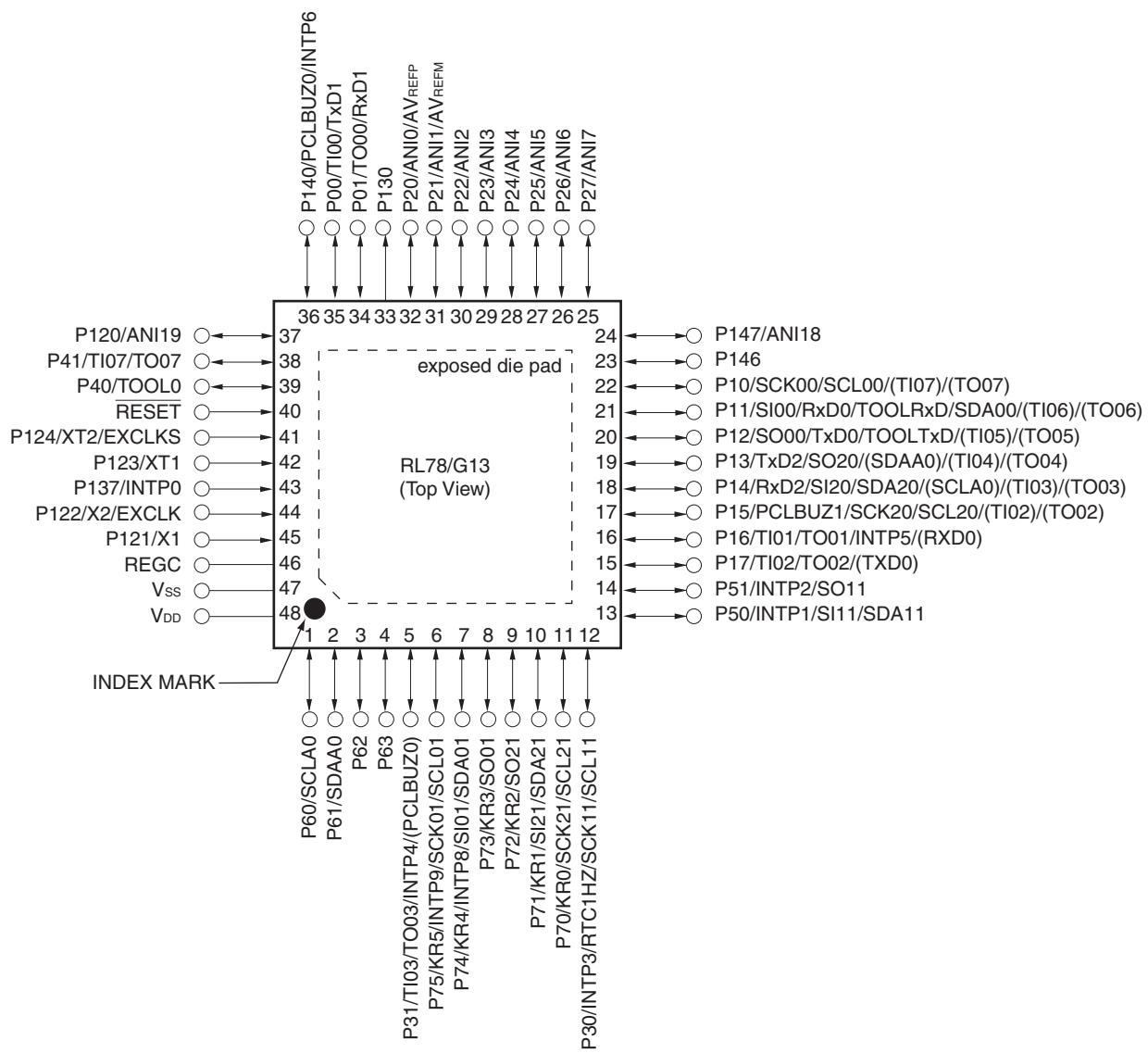
- 20-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)



Caution Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μ F).

Remark For pin identification, see **1.4 Pin Identification**.

- 48-pin plastic HWQFN (7×7 mm, 0.5 mm pitch)

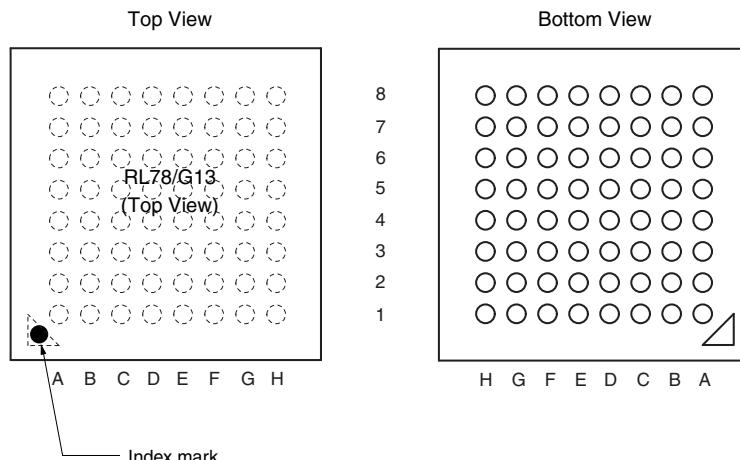


Caution Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see **1.4 Pin Identification**.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.
3. It is recommended to connect an exposed die pad to V_{SS}.

- 64-pin plastic VFBGA (4 × 4 mm, 0.4 mm pitch)



Pin No.	Name	Pin No.	Name	Pin No.	Name	Pin No.	Name
A1	P05/TI05/TO05	C1	P51/INTP2/SO11	E1	P13/TxD2/SO20/(SDAA0)/(TI04)/(TO04)	G1	P146
A2	P30/INTP3/RTC1HZ/SCK11/SCL11	C2	P71/KR1/SI21/SDA21	E2	P14/RxD2/SI20/SDA20/(SCLA0)/(TI03)/(TO03)	G2	P25/ANI5
A3	P70/KR0/SCK21/SCL21	C3	P74/KR4/INTP8/SI01/SDA01	E3	P15/SCK20/SCL20/(TI02)/(TO02)	G3	P24/ANI4
A4	P75/KR5/INTP9/SCK01/SCL01	C4	P52/(INTP10)	E4	P16/TI01/TO01/INTP5/(SI00)/(RxD0)	G4	P22/ANI2
A5	P77/KR7/INTP11/(TxD2)	C5	P53/(INTP11)	E5	P03/ANI16/SI10/RxD1/SDA10	G5	P130
A6	P61/SDAA0	C6	P63	E6	P41/TI07/TO07	G6	P02/ANI17/SO10/TxD1
A7	P60/SCLA0	C7	V _{ss}	E7	RESET	G7	P00/TI00
A8	EV _{DD0}	C8	P121/X1	E8	P137/INTP0	G8	P124/XT2/EXCLKS
B1	P50/INTP1/SI11/SDA11	D1	P55/(PCLBUZ1)/(SCK00)	F1	P10/SCK00/SCL00/(TI07)/(TO07)	H1	P147/ANI18
B2	P72/KR2/SO21	D2	P06/TI06/TO06	F2	P11/SI00/RxD0/TOOLRxDSDA00/(TI06)/(TO06)	H2	P27/ANI7
B3	P73/KR3/SO01	D3	P17/TI02/TO02/(SO00)/(TxD0)	F3	P12/SO00/TxD0/TOOLTxD/(INTP5)/(TI05)/(TO05)	H3	P26/ANI6
B4	P76/KR6/INTP10/(RxD2)	D4	P54	F4	P21/ANI1/AV _{REFM}	H4	P23/ANI3
B5	P31/TI03/TO03/INTP4/(PCLBUZ0)	D5	P42/TI04/TO04	F5	P04/SCK10/SCL10	H5	P20/ANI0/AV _{REFP}
B6	P62	D6	P40/TOOL0	F6	P43	H6	P141/PCLBUZ1/INTP7
B7	V _{DD}	D7	REGC	F7	P01/TO00	H7	P140/PCLBUZ0/INTP6
B8	EV _{SS0}	D8	P122/X2/EXCLK	F8	P123/XT1	H8	P120/ANI19

Cautions 1. Make EV_{SS0} pin the same potential as V_{ss} pin.

2. Make V_{DD} pin the potential that is higher than EV_{DD0} pin.
3. Connect the REGC pin to V_{ss} via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD} and EV_{DD0} pins and connect the V_{ss} and EV_{SS0} pins to separate ground lines.
3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.6 Outline of Functions

[20-pin, 24-pin, 25-pin, 30-pin, 32-pin, 36-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

Item	20-pin		24-pin		25-pin		30-pin		32-pin		36-pin											
	R5F1006X	R5F1016X	R5F1007X	R5F1017X	R5F1008X	R5F1018X	R5F100AX	R5F101AX	R5F100BX	R5F101BX	R5F100CX	R5F101CX										
Code flash memory (KB)	16 to 64		16 to 64		16 to 64		16 to 128		16 to 128		16 to 128											
Data flash memory (KB)	4	—	4	—	4	—	4 to 8	—	4 to 8	—	4 to 8	—										
RAM (KB)	2 to 4 ^{Note1}		2 to 4 ^{Note1}		2 to 4 ^{Note1}		2 to 12 ^{Note1}		2 to 12 ^{Note1}		2 to 12 ^{Note1}											
Address space	1 MB																					
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (High-speed main) mode: 1 to 20 MHz ($V_{DD} = 2.7$ to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz ($V_{DD} = 2.4$ to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz ($V_{DD} = 1.8$ to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz ($V_{DD} = 1.6$ to 5.5 V)																				
	High-speed on-chip oscillator	HS (High-speed main) mode: 1 to 32 MHz ($V_{DD} = 2.7$ to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz ($V_{DD} = 2.4$ to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz ($V_{DD} = 1.8$ to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz ($V_{DD} = 1.6$ to 5.5 V)																				
Subsystem clock	—																					
Low-speed on-chip oscillator	15 kHz (TYP.)																					
General-purpose registers	(8-bit register × 8) × 4 banks																					
Minimum instruction execution time	0.03125 μ s (High-speed on-chip oscillator: $f_{IH} = 32$ MHz operation)																					
	0.05 μ s (High-speed system clock: $f_{MX} = 20$ MHz operation)																					
Instruction set	<ul style="list-style-type: none"> • Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. 																					
I/O port	Total	16	20	21	26	28	32															
	CMOS I/O	13 (N-ch O.D. I/O [V_{DD} withstand voltage]: 5)	15 (N-ch O.D. I/O [V_{DD} withstand voltage]: 6)	15 (N-ch O.D. I/O [V_{DD} withstand voltage]: 6)	21 (N-ch O.D. I/O [V_{DD} withstand voltage]: 9)	22 (N-ch O.D. I/O [V_{DD} withstand voltage]: 9)	26 (N-ch O.D. I/O [V_{DD} withstand voltage]: 10)															
	CMOS input	3	3	3	3	3	3															
	CMOS output	—	—	1	—	—	—															
	N-ch O.D. I/O (withstand voltage: 6 V)	—	2	2	2	3	3															
Timer	16-bit timer	8 channels																				
	Watchdog timer	1 channel																				
	Real-time clock (RTC)	1 channel ^{Note 2}																				
	12-bit interval timer (IT)	1 channel																				
	Timer output	3 channels (PWM outputs: 2 ^{Note 3})	4 channels (PWM outputs: 3 ^{Note 3})	4 channels (PWM outputs: 3 ^{Note 3}), 8 channels (PWM outputs: 7 ^{Note 3}) ^{Note 4}																		
	RTC output	—																				

Notes 1. The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xD, R5F101xD (x = 6 to 8, A to C): Start address FF300H

R5F100xE, R5F101xE (x = 6 to 8, A to C): Start address FEF00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

2. Only the constant-period interrupt function when the low-speed on-chip oscillator clock (f_{IL}) is selected

3. The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves) (see **6.9.3 Operation as multiple PWM output function** in the RL78/G13 User's Manual).
4. When setting to PIOR = 1

(2/2)

Item	20-pin		24-pin		25-pin		30-pin		32-pin		36-pin	
	R5F1006x	R5F1016x	R5F1007x	R5F1017x	R5F1008x	R5F1018x	R5F1004Ax	R5F101Ax	R5F100Bx	R5F101Bx	R5F100Cx	R5F101Cx
Clock output/buzzer output	–		1		1		2		2		2	
	<ul style="list-style-type: none"> • 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: f_{MAIN} = 20 MHz operation) 											
8/10-bit resolution A/D converter	6 channels		6 channels		6 channels		8 channels		8 channels		8 channels	
Serial interface	<p>[20-pin, 24-pin, 25-pin products]</p> <ul style="list-style-type: none"> • CSI: 1 channel/simplified I²C: 1 channel/UART: 1 channel • CSI: 1 channel/simplified I²C: 1 channel/UART: 1 channel <p>[30-pin, 32-pin products]</p> <ul style="list-style-type: none"> • CSI: 1 channel/simplified I²C: 1 channel/UART: 1 channel • CSI: 1 channel/simplified I²C: 1 channel/UART: 1 channel • CSI: 1 channel/simplified I²C: 1 channel/UART (UART supporting LIN-bus): 1 channel <p>[36-pin products]</p> <ul style="list-style-type: none"> • CSI: 1 channel/simplified I²C: 1 channel/UART: 1 channel • CSI: 1 channel/simplified I²C: 1 channel/UART: 1 channel • CSI: 2 channels/simplified I²C: 2 channels/UART (UART supporting LIN-bus): 1 channel 											
	I ² C bus	–	1 channel	1 channel								
Multiplier and divider/multiply-accumulator	<ul style="list-style-type: none"> • 16 bits × 16 bits = 32 bits (Unsigned or signed) • 32 bits ÷ 32 bits = 32 bits (Unsigned) • 16 bits × 16 bits + 32 bits = 32 bits (Unsigned or signed) 											
DMA controller	2 channels											
Vectored interrupt sources	Internal	23	24	24	27	27	27	27	27	27	27	27
	External	3	5	5	6	6	6	6	6	6	6	6
Key interrupt	–											
Reset	<ul style="list-style-type: none"> • Reset by <u>RESET</u> pin • Internal reset by watchdog timer • Internal reset by power-on-reset • Internal reset by voltage detector • Internal reset by illegal instruction execution ^{Note} • Internal reset by RAM parity error • Internal reset by illegal-memory access 											
Power-on-reset circuit	<ul style="list-style-type: none"> • Power-on-reset: 1.51 V (TYP.) • Power-down-reset: 1.50 V (TYP.) 											
Voltage detector	<ul style="list-style-type: none"> • Rising edge : 1.67 V to 4.06 V (14 stages) • Falling edge : 1.63 V to 3.98 V (14 stages) 											
On-chip debug function	Provided											
Power supply voltage	$V_{DD} = 1.6 \text{ to } 5.5 \text{ V}$ ($T_A = -40 \text{ to } +85^\circ\text{C}$) $V_{DD} = 2.4 \text{ to } 5.5 \text{ V}$ ($T_A = -40 \text{ to } +105^\circ\text{C}$)											
Operating ambient temperature	$T_A = 40 \text{ to } +85^\circ\text{C}$ (A: Consumer applications, D: Industrial applications) $T_A = 40 \text{ to } +105^\circ\text{C}$ (G: Industrial applications)											

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.

2. The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves) (see **6.9.3 Operation as multiple PWM output function** in the RL78/G13 User's Manual).

(2/2)

Item	80-pin		100-pin		128-pin	
	R5F100Mx	R5F101Mx	R5F100Px	R5F101Px	R5F100Sx	R5F101Sx
Clock output/buzzer output	2		2		2	
	<ul style="list-style-type: none"> • 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: $f_{MAIN} = 20$ MHz operation) • 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz (Subsystem clock: $f_{SUB} = 32.768$ kHz operation) 					
8/10-bit resolution A/D converter	17 channels		20 channels		26 channels	
Serial interface	[80-pin, 100-pin, 128-pin products]		<ul style="list-style-type: none"> • CSI: 2 channels/simplified I²C: 2 channels/UART: 1 channel • CSI: 2 channels/simplified I²C: 2 channels/UART: 1 channel • CSI: 2 channels/simplified I²C: 2 channels/UART (UART supporting LIN-bus): 1 channel • CSI: 2 channels/simplified I²C: 2 channels/UART: 1 channel 			
I ² C bus	2 channels		2 channels		2 channels	
Multiplier and divider/multiply-accumulator	<ul style="list-style-type: none"> • $16 \text{ bits} \times 16 \text{ bits} = 32 \text{ bits}$ (Unsigned or signed) • $32 \text{ bits} \div 32 \text{ bits} = 32 \text{ bits}$ (Unsigned) • $16 \text{ bits} \times 16 \text{ bits} + 32 \text{ bits} = 32 \text{ bits}$ (Unsigned or signed) 					
DMA controller	4 channels					
Vectorized interrupt sources	Internal	37		37		41
	External	13		13		13
Key interrupt	8		8		8	
Reset	<ul style="list-style-type: none"> • Reset by $\overline{\text{RESET}}$ pin • Internal reset by watchdog timer • Internal reset by power-on-reset • Internal reset by voltage detector • Internal reset by illegal instruction execution ^{Note} • Internal reset by RAM parity error • Internal reset by illegal-memory access 					
Power-on-reset circuit	<ul style="list-style-type: none"> • Power-on-reset: 1.51 V (TYP.) • Power-down-reset: 1.50 V (TYP.) 					
Voltage detector	<ul style="list-style-type: none"> • Rising edge : 1.67 V to 4.06 V (14 stages) • Falling edge : 1.63 V to 3.98 V (14 stages) 					
On-chip debug function	Provided					
Power supply voltage	$V_{DD} = 1.6$ to 5.5 V ($T_A = -40$ to $+85^\circ\text{C}$) $V_{DD} = 2.4$ to 5.5 V ($T_A = -40$ to $+105^\circ\text{C}$)					
Operating ambient temperature	$T_A = 40$ to $+85^\circ\text{C}$ (A: Consumer applications, D: Industrial applications) $T_A = 40$ to $+105^\circ\text{C}$ (G: Industrial applications)					

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.

<R>

2.3.2 Supply current characteristics

(1) Flash ROM: 16 to 64 KB of 20- to 64-pin products

 $(T_A = -40$ to $+85^\circ\text{C}$, $1.6 \text{ V} \leq EV_{DD0} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{ss} = EV_{ss0} = 0 \text{ V}$) (1/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current ^{Note 1}	I_{DD1}	Operating mode HS (high-speed main) mode ^{Note 5}	$f_{IH} = 32 \text{ MHz}^{\text{Note 3}}$	Basic operation	$V_{DD} = 5.0 \text{ V}$		2.1		mA
					$V_{DD} = 3.0 \text{ V}$		2.1		mA
			$f_{IH} = 24 \text{ MHz}^{\text{Note 3}}$	Normal operation	$V_{DD} = 5.0 \text{ V}$		4.6	7.0	mA
					$V_{DD} = 3.0 \text{ V}$		4.6	7.0	mA
			$f_{IH} = 16 \text{ MHz}^{\text{Note 3}}$	Normal operation	$V_{DD} = 5.0 \text{ V}$		2.7	4.0	mA
					$V_{DD} = 3.0 \text{ V}$		2.7	4.0	mA
		LS (low-speed main) mode ^{Note 5}	$f_{IH} = 8 \text{ MHz}^{\text{Note 3}}$	Normal operation	$V_{DD} = 3.0 \text{ V}$		1.2	1.8	mA
					$V_{DD} = 2.0 \text{ V}$		1.2	1.8	mA
		LV (low-voltage main) mode ^{Note 5}	$f_{IH} = 4 \text{ MHz}^{\text{Note 3}}$	Normal operation	$V_{DD} = 3.0 \text{ V}$		1.2	1.7	mA
					$V_{DD} = 2.0 \text{ V}$		1.2	1.7	mA
		HS (high-speed main) mode ^{Note 5}	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}}, V_{DD} = 5.0 \text{ V}$	Normal operation	Square wave input		3.0	4.6	mA
					Resonator connection		3.2	4.8	mA
			$f_{MX} = 20 \text{ MHz}^{\text{Note 2}}, V_{DD} = 3.0 \text{ V}$	Normal operation	Square wave input		3.0	4.6	mA
					Resonator connection		3.2	4.8	mA
			$f_{MX} = 10 \text{ MHz}^{\text{Note 2}}, V_{DD} = 5.0 \text{ V}$	Normal operation	Square wave input		1.9	2.7	mA
					Resonator connection		1.9	2.7	mA
			$f_{MX} = 10 \text{ MHz}^{\text{Note 2}}, V_{DD} = 3.0 \text{ V}$	Normal operation	Square wave input		1.9	2.7	mA
					Resonator connection		1.9	2.7	mA
		LS (low-speed main) mode ^{Note 5}	$f_{MX} = 8 \text{ MHz}^{\text{Note 2}}, V_{DD} = 3.0 \text{ V}$	Normal operation	Square wave input		1.1	1.7	mA
					Resonator connection		1.1	1.7	mA
			$f_{MX} = 8 \text{ MHz}^{\text{Note 2}}, V_{DD} = 2.0 \text{ V}$	Normal operation	Square wave input		1.1	1.7	mA
					Resonator connection		1.1	1.7	mA
		Subsystem clock operation	$f_{SUB} = 32.768 \text{ kHz}$ ^{Note 4} $T_A = -40^\circ\text{C}$	Normal operation	Square wave input		4.1	4.9	μA
					Resonator connection		4.2	5.0	μA
			$f_{SUB} = 32.768 \text{ kHz}$ ^{Note 4} $T_A = +25^\circ\text{C}$	Normal operation	Square wave input		4.1	4.9	μA
					Resonator connection		4.2	5.0	μA
			$f_{SUB} = 32.768 \text{ kHz}$ ^{Note 4} $T_A = +50^\circ\text{C}$	Normal operation	Square wave input		4.2	5.5	μA
					Resonator connection		4.3	5.6	μA
			$f_{SUB} = 32.768 \text{ kHz}$ ^{Note 4} $T_A = +70^\circ\text{C}$	Normal operation	Square wave input		4.3	6.3	μA
					Resonator connection		4.4	6.4	μA
			$f_{SUB} = 32.768 \text{ kHz}$ ^{Note 4} $T_A = +85^\circ\text{C}$	Normal operation	Square wave input		4.6	7.7	μA
					Resonator connection		4.7	7.8	μA

(Notes and Remarks are listed on the next page.)

Notes 1. Total current flowing into V_{DD} and EV_{DD0} , including the input leakage current flowing when the level of the input pin is fixed to V_{DD} , EV_{DD0} or V_{SS} , EV_{SS0} . The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. When high-speed on-chip oscillator and subsystem clock are stopped.
3. When high-speed system clock and subsystem clock are stopped.
4. When high-speed on-chip oscillator and high-speed system clock are stopped. When $\text{AMPHS1} = 1$ (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @ 1 MHz to 32 MHz

$2.4 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @ 1 MHz to 16 MHz

LS (low-speed main) mode: $1.8 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @ 1 MHz to 8 MHz

LV (low-voltage main) mode: $1.6 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @ 1 MHz to 4 MHz

Remarks 1. f_{MX} : High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{IH} : High-speed on-chip oscillator clock frequency

3. f_{SUB} : Subsystem clock frequency (XT1 clock oscillation frequency)

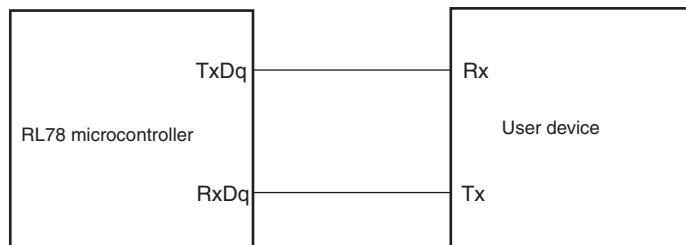
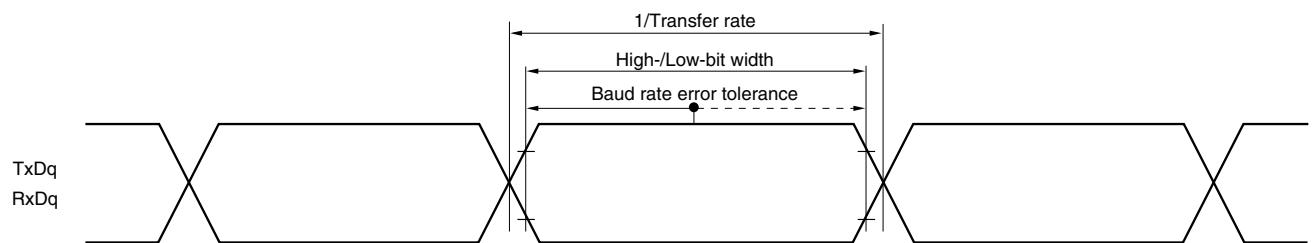
4. Except subsystem clock operation, temperature condition of the TYP. value is $T_A = 25^\circ\text{C}$

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

 $(T_A = -40$ to $+85^\circ\text{C}$, $1.6 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$) (1/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current <small>Note 1</small>	I_{DD1}	Operating mode HS (high-speed main) mode <small>Note 5</small>	$f_{IH} = 32 \text{ MHz}^{\text{Note 3}}$	Basic operation	$V_{DD} = 5.0 \text{ V}$		2.3		mA
					$V_{DD} = 3.0 \text{ V}$		2.3		mA
				Normal operation	$V_{DD} = 5.0 \text{ V}$		5.2	8.5	mA
					$V_{DD} = 3.0 \text{ V}$		5.2	8.5	mA
			$f_{IH} = 24 \text{ MHz}^{\text{Note 3}}$	Normal operation	$V_{DD} = 5.0 \text{ V}$		4.1	6.6	mA
					$V_{DD} = 3.0 \text{ V}$		4.1	6.6	mA
			$f_{IH} = 16 \text{ MHz}^{\text{Note 3}}$	Normal operation	$V_{DD} = 5.0 \text{ V}$		3.0	4.7	mA
					$V_{DD} = 3.0 \text{ V}$		3.0	4.7	mA
		LS (low-speed main) mode <small>Note 5</small>	$f_{IH} = 8 \text{ MHz}^{\text{Note 3}}$	Normal operation	$V_{DD} = 3.0 \text{ V}$		1.3	2.1	mA
					$V_{DD} = 2.0 \text{ V}$		1.3	2.1	mA
		LV (low-voltage main) mode <small>Note 5</small>	$f_{IH} = 4 \text{ MHz}^{\text{Note 3}}$	Normal operation	$V_{DD} = 3.0 \text{ V}$		1.3	1.8	mA
					$V_{DD} = 2.0 \text{ V}$		1.3	1.8	mA
		HS (high-speed main) mode <small>Note 5</small>	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}}$, $V_{DD} = 5.0 \text{ V}$	Normal operation	Square wave input		3.4	5.5	mA
					Resonator connection		3.6	5.7	mA
			$f_{MX} = 20 \text{ MHz}^{\text{Note 2}}$, $V_{DD} = 3.0 \text{ V}$	Normal operation	Square wave input		3.4	5.5	mA
					Resonator connection		3.6	5.7	mA
			$f_{MX} = 10 \text{ MHz}^{\text{Note 2}}$, $V_{DD} = 5.0 \text{ V}$	Normal operation	Square wave input		2.1	3.2	mA
					Resonator connection		2.1	3.2	mA
		LS (low-speed main) mode <small>Note 5</small>	$f_{MX} = 10 \text{ MHz}^{\text{Note 2}}$, $V_{DD} = 3.0 \text{ V}$	Normal operation	Square wave input		2.1	3.2	mA
					Resonator connection		2.1	3.2	mA
			$f_{MX} = 8 \text{ MHz}^{\text{Note 2}}$, $V_{DD} = 3.0 \text{ V}$	Normal operation	Square wave input		1.2	2.0	mA
					Resonator connection		1.2	2.0	mA
		Subsystem clock operation	$f_{SUB} = 32.768 \text{ kHz}$ <small>Note 4</small> $T_A = -40^\circ\text{C}$	Normal operation	Square wave input		4.8	5.9	μA
					Resonator connection		4.9	6.0	μA
			$f_{SUB} = 32.768 \text{ kHz}$ <small>Note 4</small> $T_A = +25^\circ\text{C}$	Normal operation	Square wave input		4.9	5.9	μA
					Resonator connection		5.0	6.0	μA
			$f_{SUB} = 32.768 \text{ kHz}$ <small>Note 4</small> $T_A = +50^\circ\text{C}$	Normal operation	Square wave input		5.0	7.6	μA
					Resonator connection		5.1	7.7	μA
			$f_{SUB} = 32.768 \text{ kHz}$ <small>Note 4</small> $T_A = +70^\circ\text{C}$	Normal operation	Square wave input		5.2	9.3	μA
					Resonator connection		5.3	9.4	μA
			$f_{SUB} = 32.768 \text{ kHz}$ <small>Note 4</small> $T_A = +85^\circ\text{C}$	Normal operation	Square wave input		5.7	13.3	μA
					Resonator connection		5.8	13.4	μA

(Notes and Remarks are listed on the next page.)

UART mode connection diagram (during communication at same potential)**UART mode bit width (during communication at same potential) (reference)**

Remarks 1. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)

2. f_{MCK} : Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(3) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output)

 $(T_A = -40$ to $+85^\circ\text{C}$, $1.6 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit	
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
SCKp cycle time	t _{KCY1}	$t_{KCY1} \geq 4/f_{CLK}$	2.7 V $\leq EV_{DD0} \leq 5.5$ V	125		500		1000		ns
			2.4 V $\leq EV_{DD0} \leq 5.5$ V	250		500		1000		ns
			1.8 V $\leq EV_{DD0} \leq 5.5$ V	500		500		1000		ns
			1.7 V $\leq EV_{DD0} \leq 5.5$ V	1000		1000		1000		ns
			1.6 V $\leq EV_{DD0} \leq 5.5$ V	—		1000		1000		ns
SCKp high-/low-level width	t _{Kh1} , t _{kl1}	4.0 V $\leq EV_{DD0} \leq 5.5$ V	t _{KCY1} /2 – 12		t _{KCY1} /2 – 50		t _{KCY1} /2 – 50		ns	
		2.7 V $\leq EV_{DD0} \leq 5.5$ V	t _{KCY1} /2 – 18		t _{KCY1} /2 – 50		t _{KCY1} /2 – 50		ns	
		2.4 V $\leq EV_{DD0} \leq 5.5$ V	t _{KCY1} /2 – 38		t _{KCY1} /2 – 50		t _{KCY1} /2 – 50		ns	
		1.8 V $\leq EV_{DD0} \leq 5.5$ V	t _{KCY1} /2 – 50		t _{KCY1} /2 – 50		t _{KCY1} /2 – 50		ns	
		1.7 V $\leq EV_{DD0} \leq 5.5$ V	t _{KCY1} /2 – 100		t _{KCY1} /2 – 100		t _{KCY1} /2 – 100		ns	
		1.6 V $\leq EV_{DD0} \leq 5.5$ V	—		t _{KCY1} /2 – 100		t _{KCY1} /2 – 100		ns	
Slp setup time (to SCKp↑) <small>Note 1</small>	t _{SIK1}	4.0 V $\leq EV_{DD0} \leq 5.5$ V	44		110		110		ns	
		2.7 V $\leq EV_{DD0} \leq 5.5$ V	44		110		110		ns	
		2.4 V $\leq EV_{DD0} \leq 5.5$ V	75		110		110		ns	
		1.8 V $\leq EV_{DD0} \leq 5.5$ V	110		110		110		ns	
		1.7 V $\leq EV_{DD0} \leq 5.5$ V	220		220		220		ns	
		1.6 V $\leq EV_{DD0} \leq 5.5$ V	—		220		220		ns	
Slp hold time (from SCKp↑) <small>Note 2</small>	t _{ksi1}	1.7 V $\leq EV_{DD0} \leq 5.5$ V	19		19		19		ns	
		1.6 V $\leq EV_{DD0} \leq 5.5$ V	—		19		19		ns	
Delay time from SCKp↓ to SOp output <small>Note 3</small>	t _{ks01}	1.7 V $\leq EV_{DD0} \leq 5.5$ V C = 30 pF ^{Note 4}		25		25		25	ns	
		1.6 V $\leq EV_{DD0} \leq 5.5$ V C = 30 pF ^{Note 4}		—		25		25	ns	

- Notes**
- When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the Slp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

(2) I²C fast mode $(T_A = -40$ to $+85^\circ\text{C}$, $1.6 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	f _{SCL}	Fast mode: $f_{CLK} \geq 3.5 \text{ MHz}$	2.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	0	400	0	400	0	400	kHz
			1.8 V $\leq EV_{DD0} \leq 5.5 \text{ V}$	0	400	0	400	0	400	kHz
Setup time of restart condition	t _{SU:STA}	2.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$		0.6		0.6		0.6		μs
		1.8 V $\leq EV_{DD0} \leq 5.5 \text{ V}$		0.6		0.6		0.6		μs
Hold time ^{Note 1}	t _{HD:STA}	2.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$		0.6		0.6		0.6		μs
		1.8 V $\leq EV_{DD0} \leq 5.5 \text{ V}$		0.6		0.6		0.6		μs
Hold time when SCLA0 = "L"	t _{LOW}	2.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$		1.3		1.3		1.3		μs
		1.8 V $\leq EV_{DD0} \leq 5.5 \text{ V}$		1.3		1.3		1.3		μs
Hold time when SCLA0 = "H"	t _{HIGH}	2.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$		0.6		0.6		0.6		μs
		1.8 V $\leq EV_{DD0} \leq 5.5 \text{ V}$		0.6		0.6		0.6		μs
Data setup time (reception)	t _{SU:DAT}	2.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$		100		100		100		μs
		1.8 V $\leq EV_{DD0} \leq 5.5 \text{ V}$		100		100		100		μs
Data hold time (transmission) ^{Note 2}	t _{HD:DAT}	2.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$		0	0.9	0	0.9	0	0.9	μs
		1.8 V $\leq EV_{DD0} \leq 5.5 \text{ V}$		0	0.9	0	0.9	0	0.9	μs
Setup time of stop condition	t _{SU:STO}	2.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$		0.6		0.6		0.6		μs
		1.8 V $\leq EV_{DD0} \leq 5.5 \text{ V}$		0.6		0.6		0.6		μs
Bus-free time	t _{BUF}	2.7 V $\leq EV_{DD0} \leq 5.5 \text{ V}$		1.3		1.3		1.3		μs
		1.8 V $\leq EV_{DD0} \leq 5.5 \text{ V}$		1.3		1.3		1.3		μs

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

<R> 2. The maximum value (MAX.) of t_{HD:DAT} is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (I_{OH1}, I_{OL1}, V_{OH1}, V_{OL1}) must satisfy the values in the redirect destination.

Remark The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode: C_b = 320 pF, R_b = 1.1 k Ω

2.6.4 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode $(T_A = -40 \text{ to } +85^\circ\text{C}, V_{PDR} \leq V_{DD} \leq 5.5 \text{ V}, V_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	V_{LVD0}	Power supply rise time	3.98	4.06	4.14	V
		Power supply fall time	3.90	3.98	4.06	V
	V_{LVD1}	Power supply rise time	3.68	3.75	3.82	V
		Power supply fall time	3.60	3.67	3.74	V
	V_{LVD2}	Power supply rise time	3.07	3.13	3.19	V
		Power supply fall time	3.00	3.06	3.12	V
	V_{LVD3}	Power supply rise time	2.96	3.02	3.08	V
		Power supply fall time	2.90	2.96	3.02	V
	V_{LVD4}	Power supply rise time	2.86	2.92	2.97	V
		Power supply fall time	2.80	2.86	2.91	V
	V_{LVD5}	Power supply rise time	2.76	2.81	2.87	V
		Power supply fall time	2.70	2.75	2.81	V
	V_{LVD6}	Power supply rise time	2.66	2.71	2.76	V
		Power supply fall time	2.60	2.65	2.70	V
	V_{LVD7}	Power supply rise time	2.56	2.61	2.66	V
		Power supply fall time	2.50	2.55	2.60	V
	V_{LVD8}	Power supply rise time	2.45	2.50	2.55	V
		Power supply fall time	2.40	2.45	2.50	V
	V_{LVD9}	Power supply rise time	2.05	2.09	2.13	V
		Power supply fall time	2.00	2.04	2.08	V
	V_{LVD10}	Power supply rise time	1.94	1.98	2.02	V
		Power supply fall time	1.90	1.94	1.98	V
	V_{LVD11}	Power supply rise time	1.84	1.88	1.91	V
		Power supply fall time	1.80	1.84	1.87	V
	V_{LVD12}	Power supply rise time	1.74	1.77	1.81	V
		Power supply fall time	1.70	1.73	1.77	V
	V_{LVD13}	Power supply rise time	1.64	1.67	1.70	V
		Power supply fall time	1.60	1.63	1.66	V
Minimum pulse width	t_{LW}		300			μs
Detection delay time					300	μs

Absolute Maximum Ratings (TA = 25°C) (2/2)

Parameter	Symbols	Conditions	Ratings	Unit	
Output current, high	I _{OH1}	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	-40	mA
		Total of all pins -170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	-70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	-100	mA
	I _{OH2}	Per pin	P20 to P27, P150 to P156	-0.5	mA
		Total of all pins		-2	mA
	I _{OL1}	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	40	mA
		Total of all pins 170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	100	mA
	I _{OL2}	Per pin	P20 to P27, P150 to P156	1	mA
		Total of all pins		5	mA
Operating ambient temperature	T _A	In normal operation mode	-40 to +105	°C	
		In flash memory programming mode			
Storage temperature	T _{stg}		-65 to +150	°C	

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin : ANI0, ANI2 to ANI14, ANI16 to ANI26

(TA = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V, Reference voltage (+) = V_{BGR}^{Note 3}, Reference voltage (-) = AV_{REFM}^{Note 4} = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		bit	
Conversion time	t _{CONV}	8-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
Zero-scale error ^{Notes 1, 2}	E _{Zs}	8-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	8-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±2.0	LSB
Differential linearity error ^{Note 1}	DLE	8-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±1.0	LSB
Analog input voltage	V _{AIN}			0		V _{BGR} ^{Note 3}	V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. Refer to 3.6.2 Temperature sensor/internal reference voltage characteristics.

4. When reference voltage (-) = V_{SS}, the MAX. values are as follows.

Zero-scale error: Add ±0.35%FSR to the MAX. value when reference voltage (-) = AV_{REFM}.

Integral linearity error: Add ±0.5 LSB to the MAX. value when reference voltage (-) = AV_{REFM}.

Differential linearity error: Add ±0.2 LSB to the MAX. value when reference voltage (-) = AV_{REFM}.

3.6.2 Temperature sensor/internal reference voltage characteristics

(TA = -40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V _{TMP25}	Setting ADS register = 80H, TA = +25°C		1.05		V
Internal reference voltage	V _{BGR}	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	F _{VTMP5}	Temperature sensor that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	t _{AMP}		5			μs

3.6.4 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode

(TA = -40 to +105°C, VPDR ≤ VDD ≤ 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	Supply voltage level	V _{LVDO}	Power supply rise time	3.90	4.06	4.22
			Power supply fall time	3.83	3.98	4.13
	V _{LVD1}	Power supply rise time	3.60	3.75	3.90	V
		Power supply fall time	3.53	3.67	3.81	V
	V _{LVD2}	Power supply rise time	3.01	3.13	3.25	V
		Power supply fall time	2.94	3.06	3.18	V
	V _{LVD3}	Power supply rise time	2.90	3.02	3.14	V
		Power supply fall time	2.85	2.96	3.07	V
	V _{LVD4}	Power supply rise time	2.81	2.92	3.03	V
		Power supply fall time	2.75	2.86	2.97	V
	V _{LVD5}	Power supply rise time	2.70	2.81	2.92	V
		Power supply fall time	2.64	2.75	2.86	V
	V _{LVD6}	Power supply rise time	2.61	2.71	2.81	V
		Power supply fall time	2.55	2.65	2.75	V
	V _{LVD7}	Power supply rise time	2.51	2.61	2.71	V
		Power supply fall time	2.45	2.55	2.65	V
Minimum pulse width	t _{LW}		300			μs
Detection delay time					300	μs

LVD Detection Voltage of Interrupt & Reset Mode

(TA = -40 to +105°C, VPDR ≤ VDD ≤ 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit		
Interrupt and reset mode	V _{LVDD0}	V _{POC2} , V _{POC1} , V _{POC0} = 0, 1, 1, falling reset voltage	2.64	2.75	2.86	V		
		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.81	2.92	3.03		
	V _{LVDD1}		Falling interrupt voltage	2.75	2.86	2.97		
			LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.90	3.02		
	V _{LVDD2}			Falling interrupt voltage	2.85	2.96		
	V _{LVDD3}			LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.90		
					Falling interrupt voltage	3.83		

3.6.5 Power supply voltage rising slope characteristics

($T_A = -40$ to $+105^\circ\text{C}$, $V_{SS} = 0$ V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	S_{VDD}				54	V/ms

Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 3.4 AC Characteristics.

3.7 RAM Data Retention Characteristics

($T_A = -40$ to $+105^\circ\text{C}$, $V_{SS} = 0$ V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V_{DDDR}		1.44 ^{Note}		5.5	V

Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.

